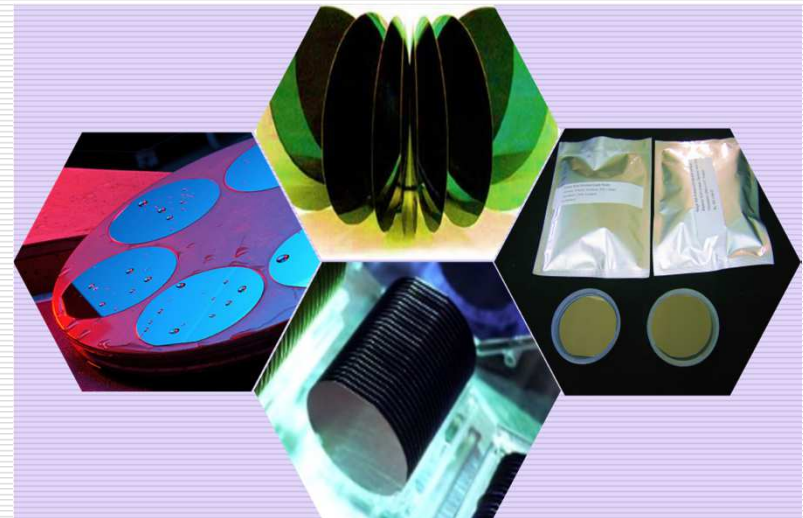


GaSb Product

Material properties	parameter	Material properties	parameter
Lattice structure	Sphalerite structure	Melting point	712°C
Band type	Direct band gap	density	5.614g/cm ³
Forbidden band width (300K)	0.725eV	Decompression	10 ⁻³ atm
Lattice constant	0.60959nm		

GaSb is mainly used as a substrate material for the preparation of thermal photovoltaic (TPV), infrared detector arrays, novel microwave devices, and the like

Type	N-type	P-type
Dopant	Te、Se、S	Zn、Ge、Si



GaSb Product

- 2-4 Dia GaSb Single crystal substrate



2英寸GaSb单晶锭



3英寸GaSb单晶锭



4英寸GaSb单晶锭



2-4英寸GaSb单晶片

GaSb Product

Cristal Electric Parameter

Dopant	Type	Carrier Con(cm-3)	Mobility (cm ² /V.s)	EPD (cm ⁻²)
Un-Dopant	p-型	(1-2)x10 ¹⁷	600-700	≤3000
Dopant-Zn	p-型	(5-100)x10 ¹⁷	200-500	≤3000
Dopant-Te	n-型	(1-20) x10 ¹⁷	2000-3500	≤3000

GaSb Product

GaSb Wafer Specification			
items	2"	3"	4"
Dia (mm)	50.5 ± 0.5	76.2 ± 0.5	100.0 ± 0.5
Thickness (um)	500 ± 25	600 ± 25	800 ± 25
Orientation	(100)/(111)	(100)/(111)	(100)/(111)
Deviation	$\pm 0.5^\circ$	$\pm 0.5^\circ$	$\pm 0.5^\circ$
Major (mm)	16 ± 2	22 ± 2	32.5 ± 2
Minor (mm)	8 ± 1	11 ± 1	18 ± 1
TTV(um)	< 10	< 10	< 15
Bow(um)	< 10	< 10	< 15
Warp(um)	< 15	< 15	< 15